OPE5294

The **OPE5294** is GaAs infrared emitting diode that is designed for low forward voltage and high reliability. This device is optimized for efficiency at emission wavelength 940nm and has a high radiant efficiency over a wide range of forward current. This device is packaged T1-3/4 plastic package and has wide beam angle with lensed package and cup frame.

FEATURES

- High-output power
- Wide beam angle
- High reliability
- Available for pulse operating
- Low cost

APPLICATIONS

- Optical emitters
- Optical switches
- Smoke sensors
- IR remote control
- IR sound transmission

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DIMENSIONS (Unit: mm)

STORAGE

• Condition: 5°C~35°C,R.H.60%

• Terms: within 3 months from production date

• Remark : Once the package is opened, the products should be used within a day. Otherwise, it should be keeping in a damp proof box with desiccants.

MAXIMUM RATINGS

 $(Ta=25^{\circ}C)$

Item	Symbol Rating		Unit	
Power Dissipation	P_{D}	150	mW	
Forward current	I_{F}	100	mA	
Pulse forward current *1	I_{FP}	1.0	A	
Reverse voltage	V_R	5.0	V	
Operating temp.	Topr.	-25~ +85	°C	
Soldering temp. *2	Tsol.	260.	°C	

^{*1.} Duty ratio = 1/100, pulse width=0.1ms.

ELECTRO-OPTICALCHARACTERISTICS

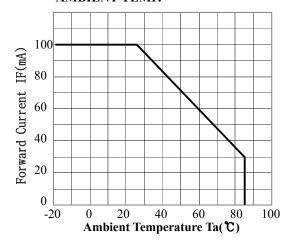
(Ta=25°C)

Item	Symbol	Conditions	Min.	Тур.	Max.	Unit
Forward voltage	V_{F}	$I_F = 100 \text{mA}$		1.4	1.7	V
Reverse current	I_R	$V_R = 5V$			10	μΑ
Capacitance	Ct	f = 1MHz		20		pF
Radiant intensity	Ie	$I_F=100mA$		30		mW/sr
Peak emission wavelength	λp	$I_F = 50 \text{mA}$		940		nm
Spectral bandwidth 50%	Δλ	$I_F = 50 \text{mA}$		45		nm
Half angle	$\Delta \Theta$	$I_F=100mA$		±22		deg.

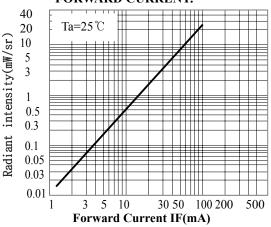
^{*} Please take proper steps in order to secure reliability and safety in required conditions and environments for this device.

^{*2.}Lead Soldering Temperature (2mm from case for 5sec.).

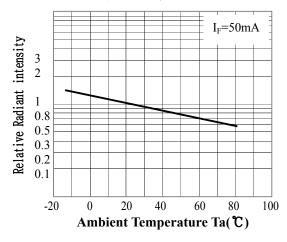
• FORWARD CURRENT Vs. AMBIENT TEMP.



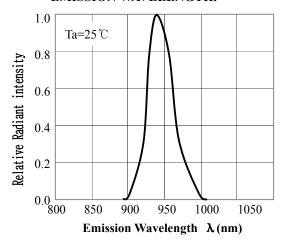
• RADIANT INTENSITY Vs. FORWARD CURRENT.



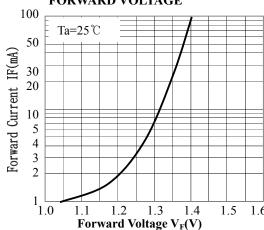
• RELATIVE RADIANT INTENSITY Vs. AMBIENT TEMP.



• RELATIVE RADIANT INTENSITY Vs. EMISSION WAVELENGTH.



• FORWARD CURRENT Vs. FORWARD VOLTAGE



ANGULAR DISPLACEMENT VS RELATIVE RADIANT INTENSITY

